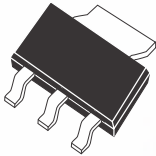


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CZT5551

NPN SILICON TRANSISTOR



SOT-223 CASE

Central
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT5551 type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high voltage amplifier applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	600	mA
Power Dissipation	P _D	2.0	W
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	62.5	°C/W

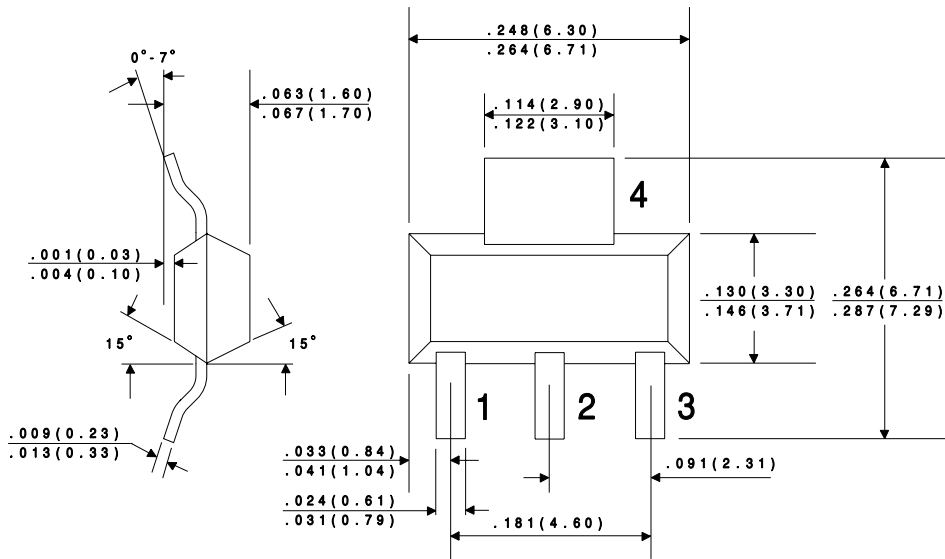
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =120V		50	nA
I _{CBO}	V _{CB} =120V, T _A =100°C		50	μA
I _{EBO}	V _{EB} =4.0V		50	nA
BV _{CB0}	I _C =100μA	180		V
BV _{CEO}	I _C =1.0mA	160		V
BV _{EBO}	I _E =10μA	6.0		V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA		0.15	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA		0.20	V
V _{BE(SAT)}	I _C =10mA, I _B =1.0mA		1.00	V
V _{BE(SAT)}	I _C =50mA, I _B =5.0mA		1.00	V
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	80		
	V _{CE} =5.0V, I _C =10mA	80	250	
	V _{CE} =5.0V, I _C =50mA	30		



SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=10V, I_C=10mA, f=100MHz$	100	300	MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		6.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=1.0MHz$		20	pF
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	50	200	
NF	$V_{CE}=5.0V, I_C=200\mu A, R_S=10\Omega$ $f=10Hz$ to $15.7kHz$		8.0	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 3) COLLECTOR